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(54) Title: FORMING CONTACTS ON SEMICONDUCTOR SUBSTRATES FOR RADIATION DETECTORS AND IMAGING DEVICES

(57) Abstract

A method, suitable for forming metal contacts (31) on a semiconductor substrate (1) at positions for defining radiation detector cells, includes the steps of forming one or more layers of material (11, 12) on a surface of the substrate with openings (23) to the substrate surface at the contact positions; forming a layer of metal (24) over the layer(s) of material and the openings; and removing metal at (28) overlying the layer(s) of material to separate individual contacts. Optionally, a passivation layer (11) to be left between individual contacts on the substrate surface, may be applied during the method. A method according to the invention prevents etchants used for removing unwanted gold (or other contact matter) coming into contact with the surface of the substrate (e.g. CdZnTe) and causing degradation of the resistive properties of that substrate. The product of the method and uses thereof are also described.

